

AM2520PD1BT03

Photodiode

DESCRIPTION

• Made with PIN silicon phototransistor chips

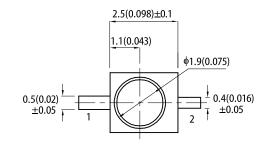
FEATURES

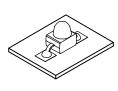
- · Mechanically and spectrally matched to the infrared emitting LED lamp
- Package: 1000 pcs / reel • Moisture sensitivity level: 3
- Halogen-free
- · Black diffused lens
- · RoHS compliant

APPLICATIONS

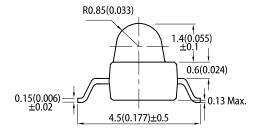
- Infrared applied systems
- Optoelectronic switches
- · Photodetector control circuits
- Sensor technology

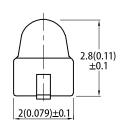
PACKAGE DIMENSIONS





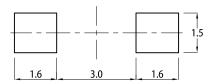






RECOMMENDED SOLDERING PATTERN

(units: mm: tolerance: ± 0.1)



- 1. All dimensions are in millimeters (inches).
- 2. Tolerance is ±0.25(0.01") unless otherwise noted.

 3. The specifications, characteristics and technical data described in the datasheet are subject to change
- without prior notice.

 4. The device has a single mounting surface. The device must be mounted according to the specifications

ABSOLUTE MAXIMUM RATINGS at T_A=25°C

Parameter	Max.Ratings	Units
Power Dissipation	150	mW
Operating Temperature	-40 to +85	°C
Storage Temperature	-40 to +85	°C

Note:
1. Relative humidity levels maintained between 40% and 60% in production area are recommended to avoid the build-up of static electricity – Ref JEDEC/JESD625-A and JEDEC/J-STD-033.

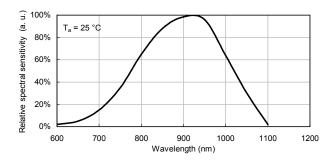


ELECTRICAL / OPTICAL CHARACTERISTICS at T_A=25°C

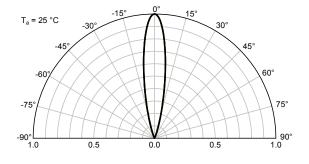
Parameter	Symbol	Min.	Тур.	Max.	Units	Test Conditions
Reverse Break down Voltage	V _{(BR)R}	33	170	-	V	$I_R = 100\mu A$ H = 0mW/cm ²
Reverse Dark Current	ID _(R)	-	-	10	nA	$V_R = 10V$ H = 0mW/cm ²
Open Circuit Voltage	V _{oc}	-	390	-	mV	$\lambda = 940$ nm H = 5mW/cm ²
Rise Time	T _R	-	6	-	nS	$V_R = 10V$ $\lambda = 940$ nm $R_L = 1000\Omega$
Fall Time	T _F	-	6	-	nS	
Light current	I _S	0.7	1.5	-	μA	$V_R = 5V$ $E_e = 0.08 \text{mW/cm}^2$ $\lambda = 940 \text{nm}$
Total Capacitance	Ст	-	5	-	pF	$V_R = 10V$ $F = 1MHZ$ $H = 0mW/cm^2$
Range of spectral bandwidth	λ _{0.1}	670	-	1070	nm	-
Wavelength of peak sensitivity	λρ	-	940	-	nm	-
Angle of half sensitivity	201/2	-	20	-	deg	-

TECHNICAL DATA

RELATIVE SPECTRAL SENSITIVITY vs. WAVELENGTH

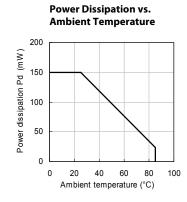


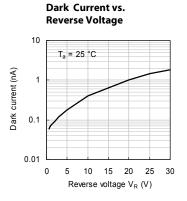
RELATIVE RADIANT SENSITIVITY vs. ANGULAR DISPLACEMENT

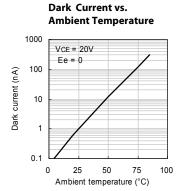


PHOTODIODE

Light Current vs. Irradiance 1000 V_R=5V T_a = 25 °C Light current Is (µA) 100 10 1 0.1 Irradiance Ee (µW/cm²)

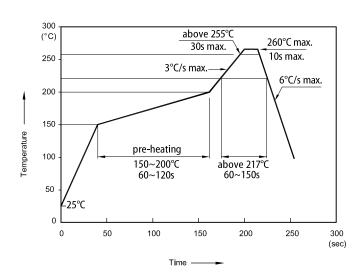






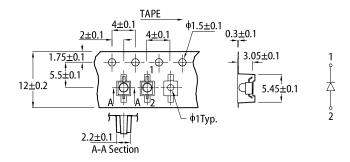


REFLOW SOLDERING PROFILE for LEAD-FREE SMD PROCESS

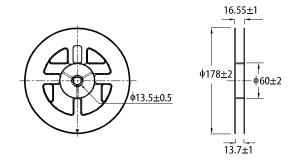


- 1. Don't cause stress to the LEDs while it is exposed to high temperature.
 2. The maximum number of reflow soldering passes is 2 times.
 3. Reflow soldering is recommended. Other soldering methods are not recommended as they might cause damage to the product.

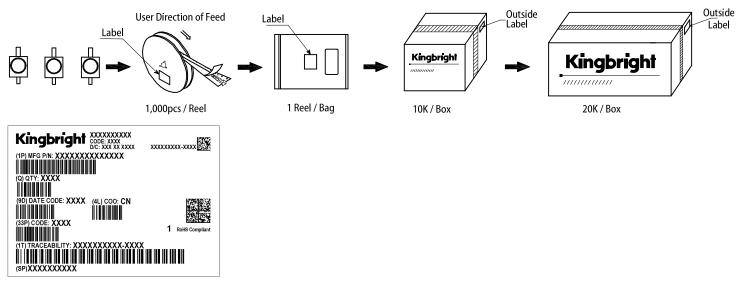
TAPE SPECIFICATIONS (units: mm)



REEL DIMENSION (units: mm)



PACKING & LABEL SPECIFICATIONS



PRECAUTIONARY NOTES

- The information included in this document reflects representative usage scenarios and is intended for technical reference only.
- The part number, type, and specifications mentioned in this document are subject to future change and improvement without notice. Before production usage customer should refer to the latest datasheet for the updated specifications.
- When using the products referenced in this document, please make sure the product is being operated within the environmental and electrical limits specified in the datasheet. If
- customer usage exceeds the specified limits, Kingbright will not be responsible for any subsequent issues.

 The information in this document applies to typical usage in consumer electronics applications. If customer's application has special reliability requirements or have life-threatening liabilities, such as automotive or medical usage, please consult with Kingbright representative for further assistance. The contents and information of this document may not be reproduced or re-transmitted without permission by Kingbright. All design applications should refer to Kingbright application notes available at https://www.KingbrightUSA.com/Application

